

KLT-231444x**Description**

KLT-231444x is long wavelength distributed feedback(DFB) laser diode(LD) sources in TO-56 package with flat window or ball lens or aspherical lens cap.

KLT-231444x consists of an InGaAsP strained multi-quantum well(MQW) LD and an InGaAs PIN-PD for output monitoring. It operates at 1310nm wavelength band and with data rates of 1.25 Gbps.

It is suitable for fabricating pigtailed LD source, TOSA(transmitter optical sub assembly), and bi-directional module.

FEATURES

- High performance strained MQW InGaAsP LD with BH(buried hetero-junction) structure
- Hermetically sealed TO-56 package with flat window or ball lens or aspherical lens cap
- High reliability and environmental endurance
- Operating wavelength of 1.3 μ m band
- Operating temperature range from -20°C to 85°C
- Data rates of 1.25Gbps

APPLICATIONS

- SONET OC-24/SDH STM-8
- 1.25Gbps Gigabit Ethernet
- Suitable for fabrication of coaxial LD module, TOSA, and Bi-Di module

Absolute Maximum Ratings

Parameter	Symbol	Min	Max	unit
Operating temperature	T_{op}	-20	85	°C
Storage temperature	T_{stg}	-40	100	°C
Peak laser forward current	I_f		150	mA
Peak laser reverse voltage	V_{rl}		2	V
Peak forward monitor PD current	I_{fp}		2	mA
Peak reverse monitor PD voltage	V_{rp}		10	V

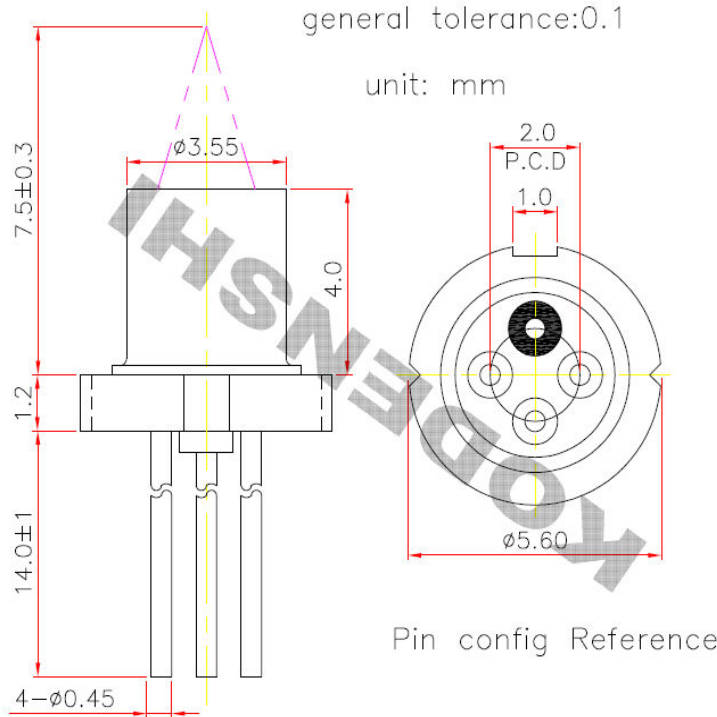
Optical and Electrical Characteristics (Top = 25°C otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Threshold current	I_{th}		7	15	mA	CW
			23	40		CW, Top = 85°C
Rated output power	P_f		5		mW	CW, kink free
Operating current	I_{op}		23	35	mA	at rated Po=5mw
			50	70		at rated Po=5mw, Top=85°C
Operating voltage	V_{op}		1.1	1.5	V	at rated Po=5mw
Slope efficiency	η	0.25	0.35		mW/mA	CW, Po=5mw
		0.15	0.2			CW, Po=5mw, Top = 85°C
Center wavelength	λ_c	1290	1310	1330	nm	at rated Po=5mw
Side mode suppression ratio	SMSR	30	40		dB	at rated Po=5mw
Optical rise and fall time	t_r		0.1	0.2	ns	20 to 80%, $I_b = I_{th}$
	t_f		0.1	0.2	ns	80 to 20%, $I_b = I_{th}$
Monitor PD current	I_m	0.05	0.25		mA	at rated Po=5mw, $V_{rp} = 1V$
Monitor PD dark current	I_d			0.1	μ A	$V_{rp} = 10V$
Monitor PD capacitance	C_t		10	20	pF	$V_{rp} = 10V, 1MHz$

Note: The engineering spec can be revised without any previous notice.

KLT-231444x

Outline Drawing

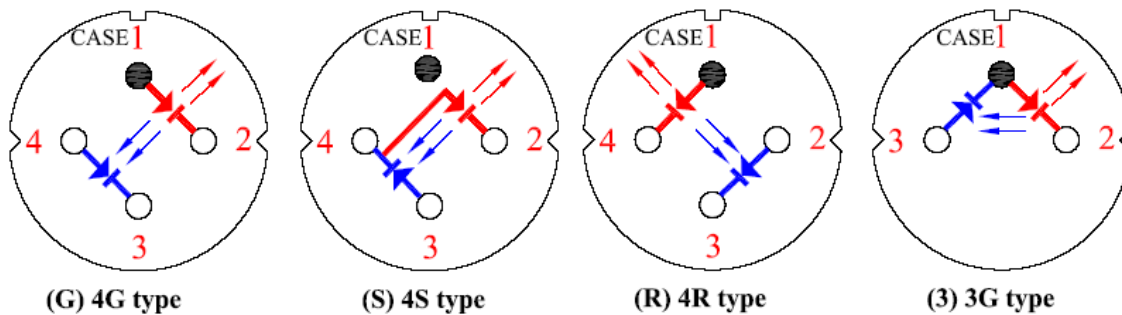


Pin connections

Pin config.	4G	4S	4R
pin no. 1	case ground/LD anode	Case ground	case ground/LD anode
pin no. 2	LD cathode	LD cathode	m-PD anode
pin no. 3	Monitor PD cathode	Monitor PD anode	m-PD cathode
pin no. 4	Monitor PD anode	LD anode/m-PD cathode	LD cathode

Ordering information

KLT	Device Type	Wavelength	Data Rate	Operating Temp.	Package type	Pin Config.
Kodenshi LD TO	1 : FP(BH)	31 : 1310 nm	4 : 1.25 Gbps	2 : -20~70	1 : 1.5 mm ball lens	S : 4S type
	2 : DFB	55 : 1550 nm	5 : 2.5 Gbps	4 : -20~85	2 : 2.0mm ball lens	G : 4G type
	3 : CWDM-DFB	49 : 1490 nm		5 : -40~85	3 : flat window	R : 4R type
	4 : AR LD	xx:1xx0nm ±3nm(CWDM)			4 : aspheric lens	3: 3G
		yB(band):O,E,S,C,L,NI,NC				



Pin configuration of LD TO Package (Bottom view)